



# CMOS High Voltage Logic – CD4046B

## CMOS Micropower Phase Locked Loop (PLL) in bare die form

Rev 1.0  
21/09/18

### Description

The CD4046B phase locked loop consists of two phase comparators, a voltage-controlled oscillator (VCO), source follower and zener diode. The comparators have a common signal input amplifier and common comparator input. The zener diode is used for power supply regulation if required. Applications include FM and FSK modulation / demodulation, frequency synthesis and multiplication, frequency discrimination, tone decoding, data synchronization and conditioning, voltage-to-frequency conversion and motor speed control.

### Features:

- Choice of two Phase Comparators:
  - Exclusive Or Gate, duty cycle limited
  - Rising edge switching, duty cycle unlimited
- Buffered outputs compatible with MHTL and Low power TTL
- VCO inhibit control for ON-OFF keying and ultra-low standby power consumption
- Source-follower output of VCO control input
- Integrated zener diode to assist supply regulation
- Supply voltage range: 3V to 18V
- Symmetrical output characteristics

### Ordering Information

The following part suffixes apply:

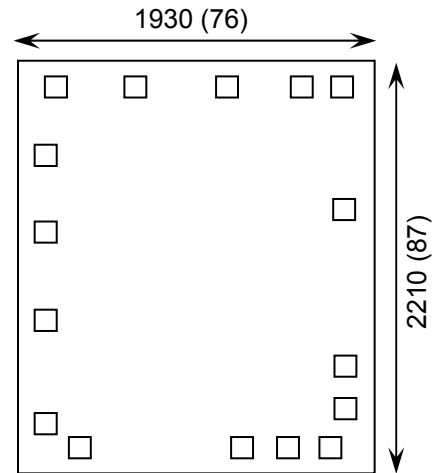
- No suffix - MIL-STD-883 /2010B Visual Inspection
- "H" - MIL-STD-883 /2010B Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" - MIL-STD-883 /2010A Visual Inspection (Space) + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

[www.siliconsupplies.com/quality/bare-die-lot-qualification](http://www.siliconsupplies.com/quality/bare-die-lot-qualification)

### Die Dimensions in $\mu\text{m}$ (mils)



### Supply Formats:

- Default – Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape – On request
- Unsawn Wafer – On request
- Die Thickness  $\leftrightarrow$  635 $\mu\text{m}$ (25 Mils) – On request
- Assembled into Ceramic Package – On request

### Mechanical Specification

Die Size (Unsawn)	1930 x 2210 76 x 87	$\mu\text{m}$ mils
Minimum Bond Pad Size	106 x 106 4.17 x 4.17	$\mu\text{m}$ mils
Die Thickness	635 ( $\pm$ 20) 25 ( $\pm$ 0.79)	$\mu\text{m}$ mils
Top Metal Composition	Al 1%Si 1.1 $\mu\text{m}$	
Back Metal Composition	N/A – Bare Si	

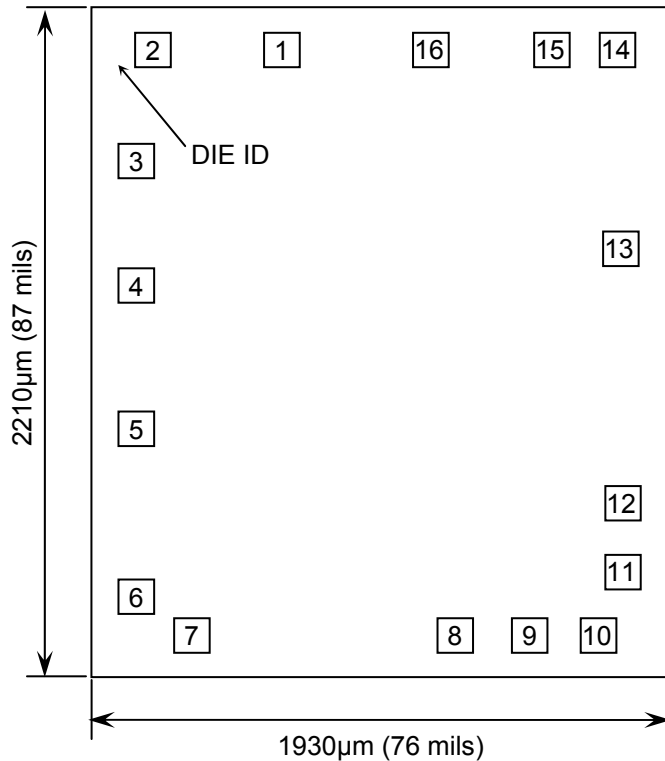




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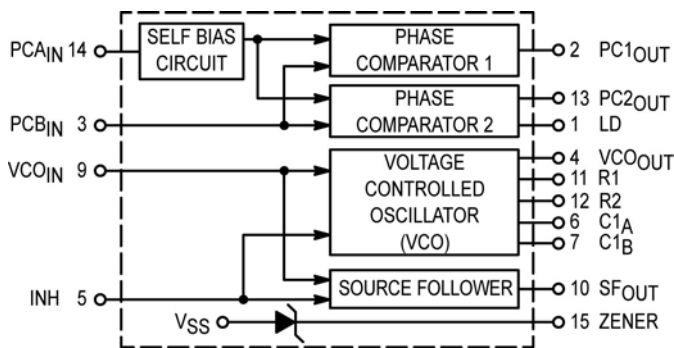
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## Pad Layout and Functions



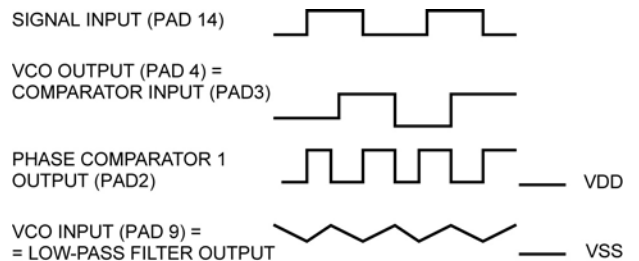
PAD	FUNCTION
1	LD
2	PC1 <sub>OUT</sub>
3	PCB <sub>IN</sub>
4	VCO <sub>OUT</sub>
5	INH
6	C1 <sub>A</sub>
7	C1 <sub>B</sub>
8	V <sub>SS</sub>
9	VCO <sub>IN</sub>
10	SF <sub>OUT</sub>
11	R1
12	R2
13	PC2 <sub>OUT</sub>
14	PCA <sub>IN</sub>
15	ZENER
16	V <sub>DD</sub>
CONNECT CHIP BACK TO V <sub>DD</sub> OR FLOAT	

## Block Diagram



Pad 1 = V<sub>DD</sub>  
Pad 8 = V<sub>SS</sub>

## PLL Waveforms



Typical waveforms for CMOS PLL with phase comparator in locked condition of  $f_{osc}$





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## Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to V <sub>SS</sub> )	V <sub>DD</sub>	-0.5 to +20	V
DC Input Voltage (Referenced to V <sub>SS</sub> )	V <sub>IN</sub>	-0.5 to V <sub>DD</sub> +0.5	V
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C
Input Current (per Pad)	I <sub>IN</sub>	±10	mA
Power Dissipation in Still Air	P <sub>D</sub>	500	mW

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

## Recommended Operating Conditions<sup>3</sup> (Voltages referenced to V<sub>SS</sub>)

PARAMETER	SYMBOL	MIN	MAX	UNITS
Supply Voltage	V <sub>DD</sub>	3	18	V
DC Input Voltage, Output Voltage	V <sub>IN</sub> , V <sub>OUT</sub>	0	V <sub>DD</sub>	V
Operating Temperature Range	T <sub>A</sub>	-55	+125	°C

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>IN</sub> and V<sub>OUT</sub> should be constrained to the range V<sub>SS</sub> ≤ (V<sub>IN</sub> or V<sub>OUT</sub>) ≤ V<sub>DD</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V<sub>SS</sub> or V<sub>DD</sub>). Unused outputs must be left open.

## DC Electrical Characteristics (Voltages referenced to V<sub>SS</sub>)

PARAMETER	SYMBOL	V <sub>DD</sub>	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE <sup>4</sup>	
Minimum High-Level Input Voltage	V <sub>IH</sub>	5V	V <sub>OUT</sub> = 0.5V or 4.5V	3.5	3.5	3.5	V
		10V	V <sub>OUT</sub> = 1V or 9V	7	7	7	
		15V	V <sub>OUT</sub> = 1.5V or 13.5V	11	11	11	
Maximum Low-Level Input Voltage	V <sub>IL</sub>	5V	V <sub>OUT</sub> = 4.5V or 0.5V	1.5	1.5	1.5	V
		10V	V <sub>OUT</sub> = 9V or 1V	3	3	3	
		15V	V <sub>OUT</sub> = 13.5V or 1.5V	4.0	4.0	4.0	
Minimum High-Level Output Voltage	V <sub>OH</sub>	5V	V <sub>IN</sub> = 0 or V <sub>DD</sub>	4.95	4.95	4.95	V
		10V		9.95	9.95	9.95	
		15V		14.95	14.95	14.95	
Maximum Low-Level Output Voltage	V <sub>OL</sub>	5V	V <sub>IN</sub> = V <sub>DD</sub> or 0	0.05	0.05	0.05	V
		10V		0.05	0.05	0.05	
		15V		0.05	0.05	0.05	
Maximum Input Leakage Current	I <sub>IN</sub>	15V	V <sub>IN</sub> = V <sub>DD</sub> or V <sub>SS</sub>	±0.1	±0.1	±1.0	µA

4. -55°C ≤ T<sub>J</sub> ≤ +125°C





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## DC Electrical Characteristics (Voltages referenced to $V_{SS}$ )

PARAMETER	SYMBOL	$V_{DD}$	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE <sup>4</sup>	
Minimum Output Drive (Source)	$I_{OH}$	5	$V_{OH} = 2.5V$	-1.2	-1.0	-0.7	mA
		5	$V_{OH} = 4.6V$	-0.25	-0.2	-0.14	
		10	$V_{OH} = 9.5V$	-0.65	-0.5	-0.35	
		15	$V_{OH} = 13.5V$	-1.8	-1.5	-1.1	
Minimum Output Drive (Sink)	$I_{OL}$	5	$V_{OL} = 0.4V$	0.64	0.51	0.36	mA
		10	$V_{OL} = 0.5V$	1.6	1.3	0.9	
		15	$V_{OL} = 1.5V$	4.2	3.4	2.4	
Maximum Quiescent Supply Current	$I_{DD}$	5V	INH = $PCA_{IN} = V_{DD}$ , Zener = $VCO_{IN} = 0V$ , $PCB_{IN} = V_{DD}$ or $0V$ , $I_{OUT} = 0\mu A$	5	5	150	$\mu A$
		10V		10	10	300	
		15V		20	20	600	
Noise Immunity Margin	-	5V	"1" & "0" level	1	-	-	V
		10V		1	-	-	
		15V		1	-	-	

## AC Electrical Characteristics<sup>5</sup> $T_J = 25^\circ C$ unless otherwise specified

PARAMETER	SYMBOL	$V_{DD}$	CONDITIONS	MIN	TYPICAL	MAX	UNITS
Transition Time, Low to High	$t_{TLH}$	5V	$C_L = 50pF$	-	180	350	ns
		10V		-	90	150	
		15V		-	65	110	
Transition Time, High to Low	$t_{THL}$	5V	$C_L = 50pF$	-	100	175	ns
		10V		-	50	75	
		15V		-	37	55	

### PHASE COMPARATORS 1 AND 2

PARAMETER	SYMBOL	$V_{DD}$	CONDITIONS	MIN	TYPICAL	MAX	UNITS
Input Resistance	$R_{IN}$	5V	$PCA_{IN}$	1.0	2.0	-	$M\Omega$
		10V		0.2	0.4	-	
		15V		0.1	0.2	-	
		15V	$PCB_{IN}$	150	1500	-	
Minimum Input Sensitivity	$V_{IN}$	5V	AC coupled - $PCA_{IN}$ , C Series = $1000pF$ , $f = 50kHz$	-	200	300	mV p-p
		10V		-	400	600	
		15V		-	700	1050	
		5 - 15V	DC coupled, $PCA_{IN}, PCB_{IN}$	See noise immunity			

### VOLTAGE CONTROLLED OSCILLATOR (VCO)

PARAMETER	SYMBOL	$V_{DD}$	CONDITIONS	MIN	TYPICAL	MAX	UNITS
Maximum Frequency	$f_{MAX}$	5V	$VCO_{IN} = V_{DD}$ , $C1 = 50pF$ , $R1 = 5k\Omega, R2 = \infty$	0.5	0.7	-	MHz
		10V		1.0	1.4	-	
		15V		1.4	1.9	-	

5. Not production tested in die form, characterized by chip design and tested in package.





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## AC Electrical Characteristics<sup>5</sup> $T_J = 25^\circ\text{C}$ unless otherwise specified

PARAMETER	SYMBOL	V <sub>DD</sub>	CONDITIONS	MIN	TYPICAL	MAX	UNITS
Temperature - Frequency stability	-	5V	R2 = ∞,	-	0.12	-	%/ $^\circ\text{C}$
		10V		-	0.04	-	
		15V		-	0.015	-	
Linearity	-	5V	R2 = ∞, VCO <sub>IN</sub> = 2.5V ± 0.3V, R1 > 10kΩ	-	1	-	%
		10V	R2 = ∞, VCO <sub>IN</sub> = 5V ± 2.5V, R1 > 400kΩ	-	1	-	
		15V	R2 = ∞, VCO <sub>IN</sub> = 7.5V ± 5V, R1 ≥ 1000kΩ	-	1	-	
Output Duty Cycle	-	5 -15V	-	-	50	-	%
Input Resistance	R <sub>IN</sub>	15	VCO <sub>IN</sub>	150	1500	-	MΩ
<b>SOURCE FOLLOWER</b>							
PARAMETER	SYMBOL	V <sub>DD</sub>	CONDITIONS	MIN	TYPICAL	MAX	UNITS
Offset Voltage	V <sub>OS</sub>	5V	VCO <sub>IN</sub> – SF <sub>OUT</sub> , RSF > 500kΩ	-	1.65	2.2	V
		10V		-	1.65	2.2	
		15V		-	1.65	2.2	
Linearity	-	5V	VCO <sub>IN</sub> = 2.5V ± 0.3V, RSF > 50kΩ	-	0.1	300	%
		10V	VCO <sub>IN</sub> = 5V ± 2.5V, RSF > 50kΩ	-	0.6	600	
		15V	VCO <sub>IN</sub> = 7.5V ± 5V, RSF > 50kΩ	-	0.8	1050	
<b>ZENER DIODE</b>							
Zener Voltage	V <sub>Z</sub>	-	I <sub>Z</sub> = 50μA	6.7	7	7.3	V
Dynamic Resistance	R <sub>Z</sub>	-	I <sub>Z</sub> = 1mA	-	100	-	Ω

5. Not production tested in die form, characterized by chip design and tested in package.

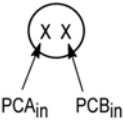
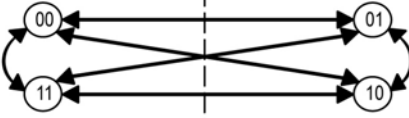
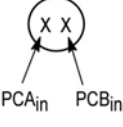
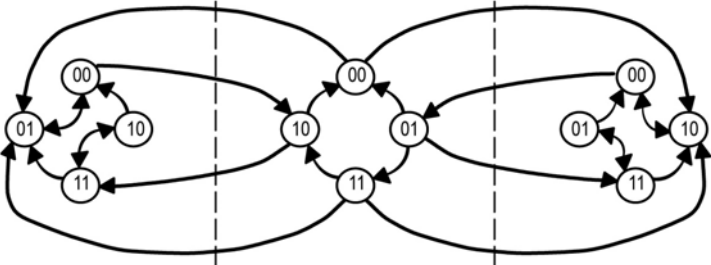




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## Phase Comparator State Diagram & Design Info

PHASE COMPARATOR 1		
Input Stage 		
PC1 <sub>out</sub>	0	1
PHASE COMPARATOR 2		
Input Stage 		
PC2 <sub>out</sub>	0	3-State Output Disconnected
LD (Lock Detect)	0	1
LD	0	0
Characteristic	Using Phase Comparator 1	Using Phase Comparator 2
No signal on input PCA <sub>in</sub> .	VCO in PLL system adjusts to center frequency (f <sub>0</sub> ).	VCO in PLL system adjusts to minimum frequency (f <sub>min</sub> ).
Phase angle between PCA <sub>in</sub> and PCB <sub>in</sub> .	90° at center frequency (f <sub>0</sub> ), approaching 0° and 180° at ends of lock range (2f <sub>L</sub> )	Always 0° in lock (positive rising edges).
Locks on harmonics of center frequency.	Yes	No
Signal input noise rejection.	High	Low
Lock frequency range (2f <sub>L</sub> ).	The frequency range of the input signal on which the loop will stay locked if it was initially in lock; 2f <sub>L</sub> = full VCO frequency range = f <sub>max</sub> - f <sub>min</sub> .	
Capture frequency range (2f <sub>C</sub> ).	The frequency range of the input signal on which the loop will lock if it was initially out of lock.	
	Depends on low-pass filter characteristics (see low pass example). f <sub>C</sub> ≤ f <sub>L</sub>	f <sub>C</sub> = f <sub>L</sub>
Center frequency (f <sub>0</sub> ).	The frequency of VCO <sub>out</sub> , when VCO <sub>in</sub> = 1/2 V <sub>DD</sub>	
VCO output frequency (f).	$f_{min} = \frac{1}{R_2(C_1 + 32 \text{ pF})} \quad (\text{VCO input} = V_{SS})$ $f_{max} = \frac{1}{R_1(C_1 + 32 \text{ pF})} + f_{min} \quad (\text{VCO input} = V_{DD})$	
Note: These equations are intended to be a design guide. Since calculated component values may be in error by as much as a factor of 4, laboratory experimentation may be required for fixed designs. Part to part frequency variation with identical passive components is typically less than ± 20%.	Where: 10K ≤ R <sub>1</sub> ≤ 1 M 10K ≤ R <sub>2</sub> ≤ 1 M 100pF ≤ C <sub>1</sub> ≤ .01 μF	

Refer to General Phase-Locked Loop Connections and Waveforms

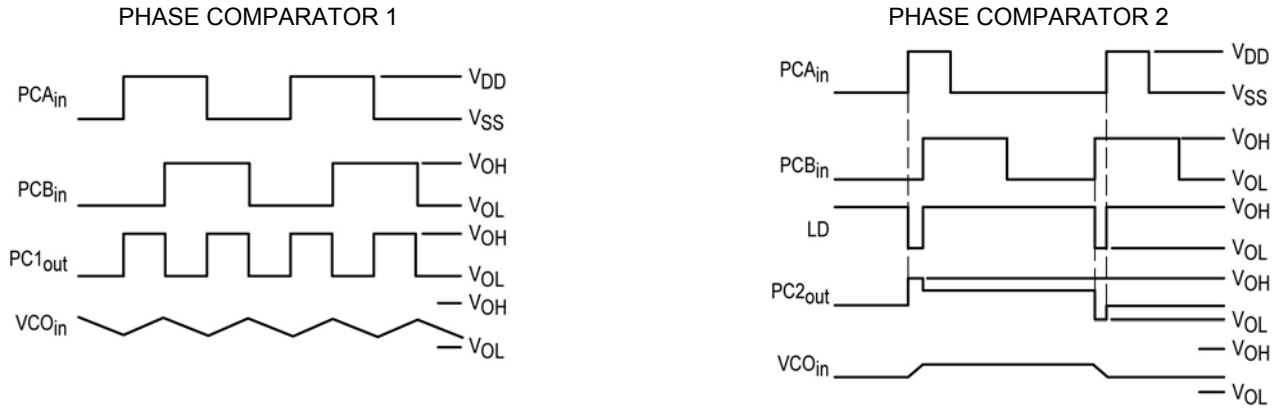




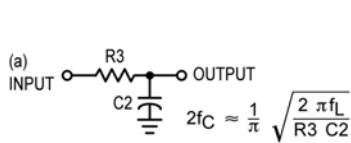
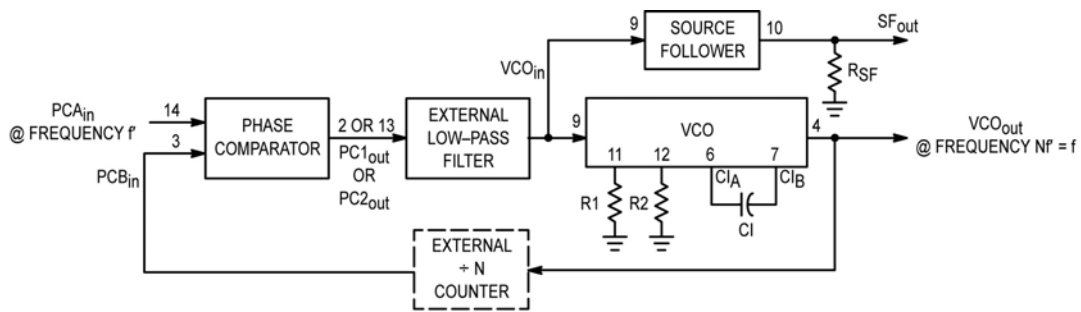
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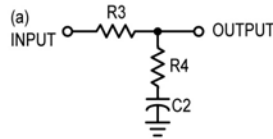
## General Phase-Locked Loop Connections and Waveforms



## Low Pass Filter Example



Typical Low-Pass Filters



Typically:

$$R_4 C_2 = \frac{6N}{f_{\max}} - \frac{N}{2\pi \Delta f}$$

$$(R_3 + 3,000\Omega) C_2 = \frac{100N\Delta f}{f_{\max}^2} - R_4 C_2$$

$$\Delta f = f_{\max} - f_{\min}$$

NOTE: Sometimes R3 is split into two series resistors each R3 + 2. A capacitor C<sub>C</sub> is then placed from the midpoint to ground. The value for C<sub>C</sub> should be such that the corner frequency of this network does not significantly affect ω<sub>n</sub>. In Figure B, the ratio of R3 to R4 sets the damping, R4 ≅ (0.1)(R3) for optimum results.

Definitions: N = Total division ratio in feedback loop  
 $K_{\phi} = V_{DD}/\pi$  for Phase Comparator 1  
 $K_{\phi} = V_{DD}/4\pi$  for Phase Comparator 2  
 $K_{VCO} = \frac{2\pi \Delta f_{VCO}}{V_{DD} - 2V}$   
 for a typical design  $\omega_n \cong \frac{2\pi f_r}{10}$  (at phase detector input)  
 $\zeta \cong 0.707$

LOW-PASS FILTER

Filter A	Filter B
$\omega_n = \sqrt{\frac{K_{\phi} K_{VCO}}{NR_3 C_2}}$	$\omega_n = \sqrt{\frac{K_{\phi} K_{VCO}}{NC_2(R_3 + R_4)}}$
$\zeta = \frac{N\omega_n}{2K_{\phi} K_{VCO}}$	$\zeta = 0.5 \omega_n (R_3 C_2 + \frac{N}{K_{\phi} K_{VCO}})$
$F(s) = \frac{1}{R_3 C_2 S + 1}$	$F(s) = \frac{R_3 C_2 S + 1}{S(R_3 C_2 + R_4 C_2) + 1}$





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